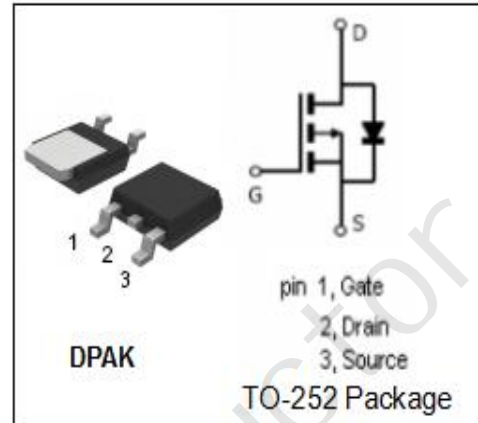


• FEATURES

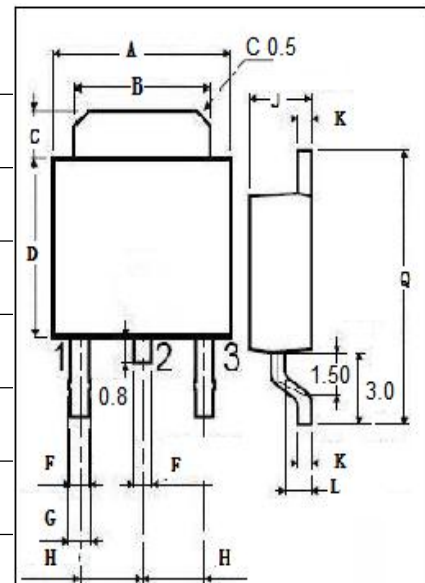
- TO-252(DPAK) packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation


• APPLICATIONS

- Power supply
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	-60	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous@T _c =25°C T _c =100°C	-26 -18	A
I _{DM}	Drain Current-Single Pulsed	-60	A
P _D	Total Dissipation	60	W
T _j	Operating Junction Temperature	175	°C
T _{stg}	Storage Temperature	-55~175	°C



DIM	mm	
	MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	2.5	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	50	°C/W

ELECTRICAL CHARACTERISTICS
 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=-0.25mA$	-60			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=-0.25mA$	-1.2		-2.4	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=-10V; I_D=-20A$		32	40	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V; V_{GS}=0V; T_j=25^{\circ}\text{C}$ $T_j=55^{\circ}\text{C}$			-1 -5	μA
V_{SDF}	Diode forward voltage	$I_{SD}=-1A, V_{GS}=0V$			-1	V

单击下面可查看定价，库存，交付和生命周期等信息

[>>JSMSEMI\(杰盛微\)](#)